TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

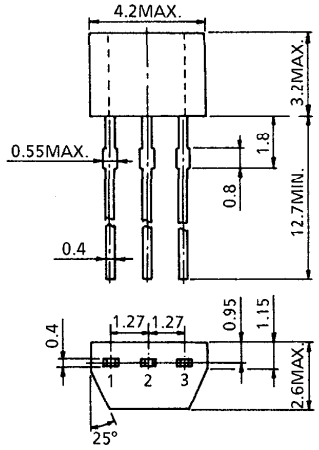
2SC3267

POWER AMPLIFIER APPLICATIONS

POWER SWICHING APPLICATIONS

- Low Saturation Voltage : $V_{CE\ (sat)} = 0.5V$ (Max.) @$I_C = 2A$
- Complementary to 2SA1297

Unit in mm



1. EMITTER
2. COLLECTOR
3. BASE

JEDEC	—
EIAJ	—
TOSHIBA	2-4E1A

Weight : 0.13g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	2	A
Base Current	I_B	0.5	A
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	−55~150	°C

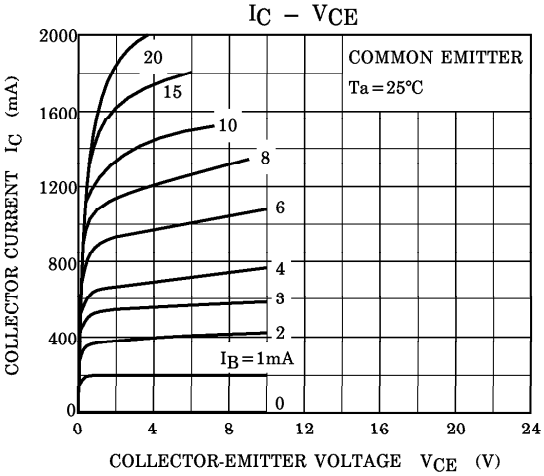
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=20V$, $I_E=0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=6V$, $I_C=0$	—	—	0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)\ CEO}$	$I_C=10mA$, $I_B=0$	20	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)\ EBO}$	$I_E=0.1mA$, $I_C=0$	6	—	—	V
DC Current Gain	$h_{FE\ (1)}$ (Note)	$V_{CE}=2V$, $I_C=100mA$	120	—	700	
	$h_{FE\ (2)}$	$V_{CE}=2V$, $I_C=2A$	75	—	—	
Collector-Emitter Sturation Voltage	$V_{CE\ (sat)}$	$I_C=2A$, $I_B=0.1A$	—	—	0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=2V$, $I_C=0.1A$	—	—	0.85	V
Transition Frequency	f_T	$V_{CE}=2V$, $I_C=0.5A$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V$, $I_E=0$, f=1MHz	—	30	—	pF

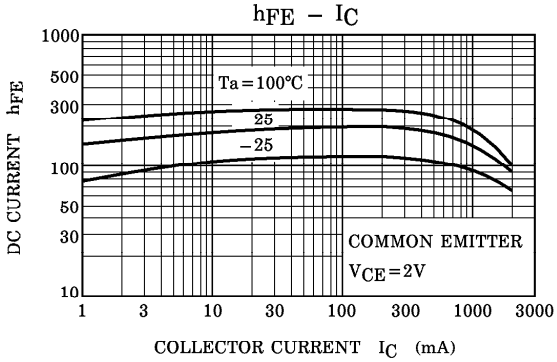
Note : $h_{FE\ (1)}$ Classification Y : 120~240, GR : 200~400, BL : 350~700

961001EAA2

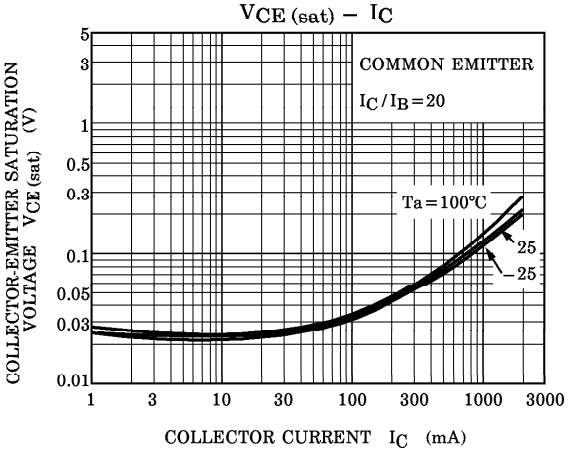
I_C – V_{CE}



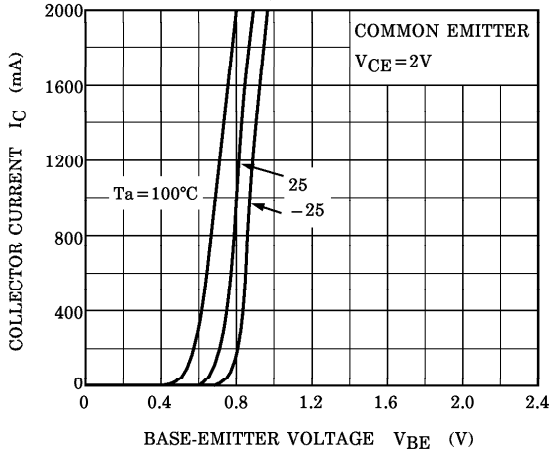
h_{FE} – I_C



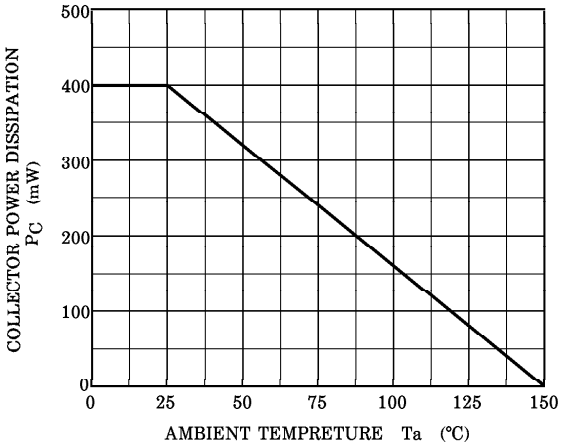
$V_{CE\,(sat)}$ – I_C



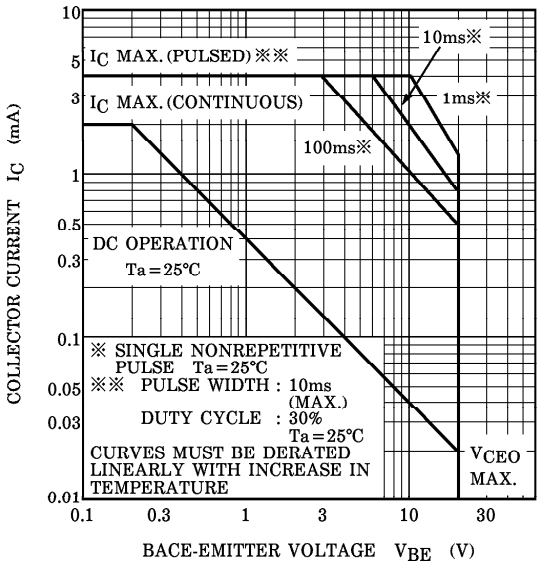
I_C – V_{BE}



P_C – Ta



SAFE OPERATING AREA



961001EAA2'